



N-Channel Depletion-Mode Vertical DMOS FETs

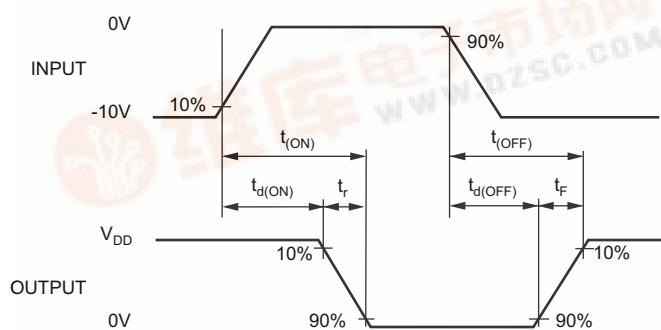
Features

- ▶ Very low gate threshold voltage
- ▶ Design to be source-driven
- ▶ Low switching losses
- ▶ Low effective output capacitance
- ▶ Design for inductive load
- ▶ Well matched for low second harmonic

Applications

- ▶ Medical ultrasound beamforming
- ▶ Ultrasonic array focusing transmitter
- ▶ Piezoelectric transducer waveform drivers
- ▶ High speed arbitrary waveform generator
- ▶ Normally-on switches
- ▶ Solid state relays
- ▶ Constant current sources
- ▶ Power supply circuits

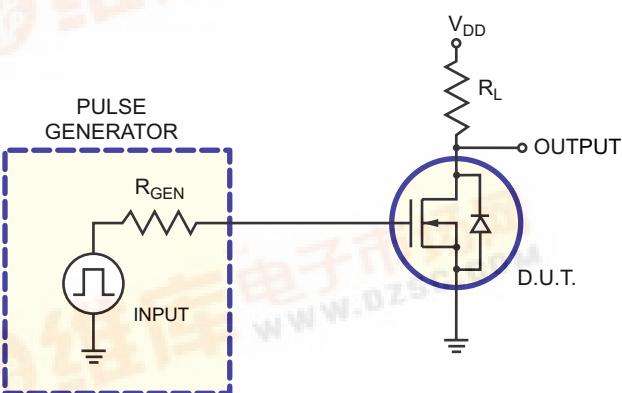
Switching Waveforms and Test Circuit



General Description

The Supertex DN2625 is a low threshold depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.



Thermal Characteristics

Package	I_D (continuous) ¹ (A)	I_D (pulsed) (A)	R_{ejA} (°C/W)	R_{ejC} (°C/W)	I_{DR} (A)	I_{DRM} (A)
D-PAK	1.1	3.3	50	5.5	1.1	3.3
14-Lead QFN	45	4.0				

1. I_D (continuous) is limited by Max. T_j

2. 4-layer, 1oz, 3x4inch PCB, with 20-via for drain pad.

Ordering Information

Device	Package Options		BV_{DSX}/BV_{DGX} (V)	$V_{GS(OFF)}$ (max V)	$I_{DS}(V_{GS}=0.9V)$ (min A)
	TO-252 (D-PAK)	14-Lead QFN 5x5mm body, 1.0mm height (max), 1.27mm pitch			
DN2625	DN2625K4-G	DN2625K6-G	250	-2.1	3.3

-G indicates package is RoHS compliant ('Green')



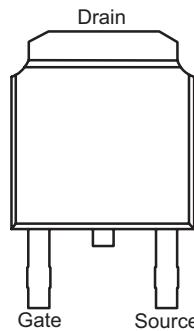
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	250V
Drain-to-gate voltage	250V
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

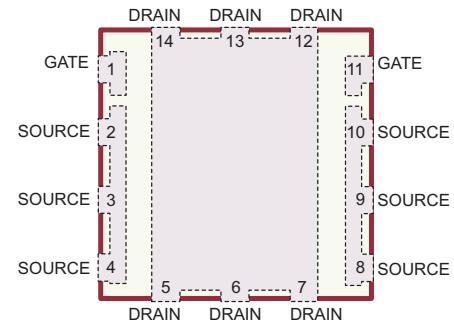
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

*Distance of 1.6mm from case for 10 seconds.

Pin Configurations



TO-252 D-PAK
(top view)



14-Lead QFN
(top view)

Product Marking



YY = Year Sealed
WW = Week Sealed
L = Lot Number
____ = "Green" Packaging

TO-252 D-PAK



L = Lot Number
YY = Year Sealed
WW = Week Sealed
A = Assembler ID
C = Country of Origin
____ = "Green" Packaging

14-Lead QFN

Electrical Characteristics @25°C unless otherwise specified

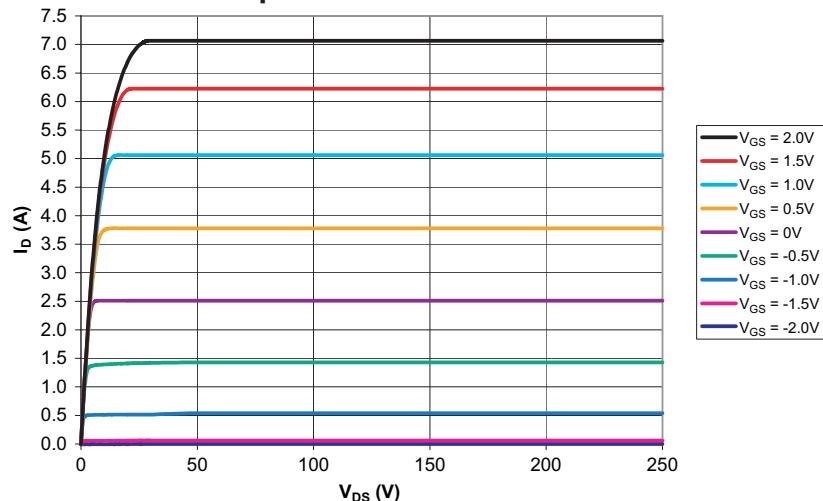
Symbol	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSX}	Drain-to-source breakdown voltage	250	-	-	V	$V_{GS} = -2.5V, I_D = 50\mu A$
BV_{DGX}	Drain-to-gate breakdown voltage	250	-	-	V	$V_{GS} = -2.5V, I_D = 50\mu A$
$V_{GS(OFF)}$	Gate-to-source OFF voltage	-1.5	-	-2.1	V	$V_{DS} = 15V, I_D = 100\mu A$
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with temperature	-	-	4.5	mV/°C	$V_{DS} = 15V, I_D = 100\mu A$

Electrical Characteristics (cont) @25°C unless otherwise specified

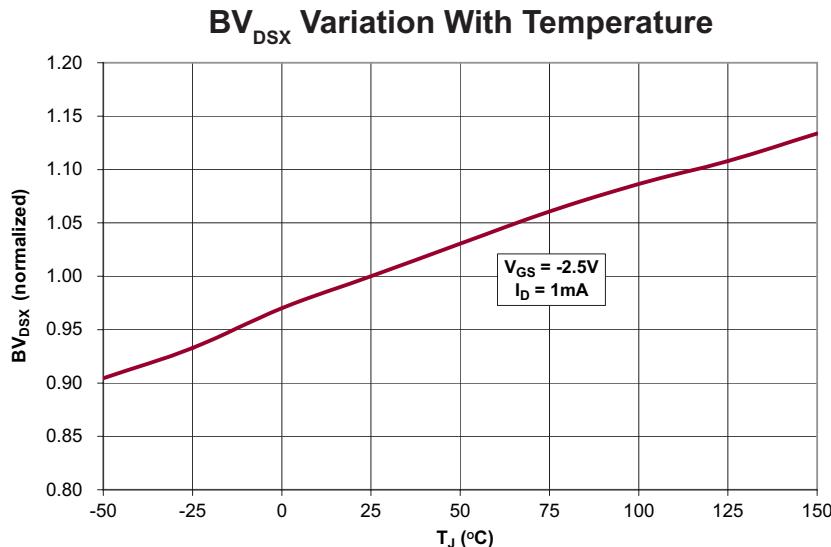
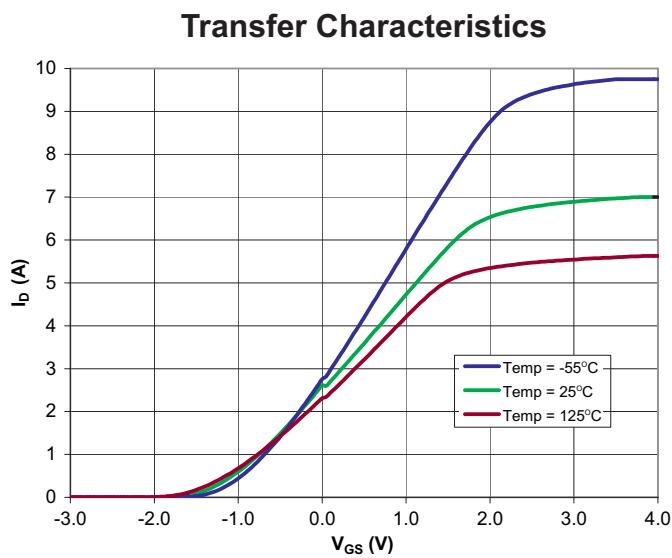
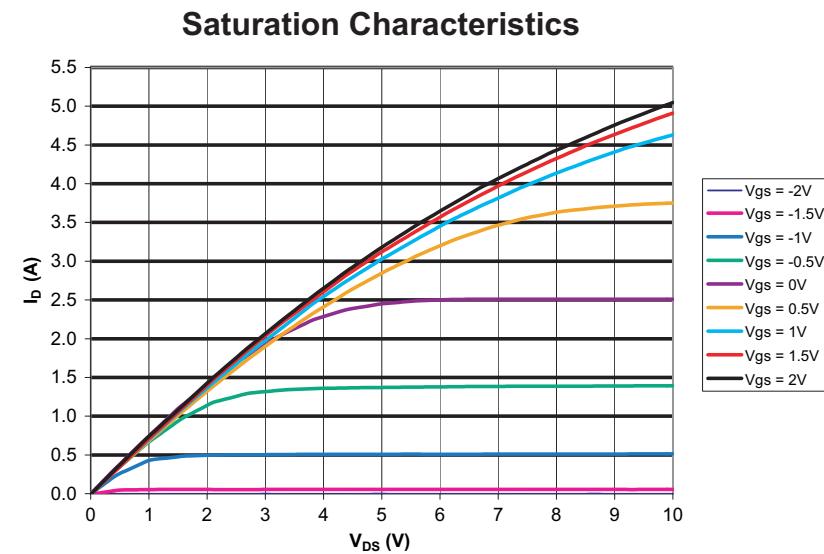
Symbol	Parameter	Min	Typ	Max	Units	Conditions
I_{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
$I_{D(OFF)}$	Drain-to-source leakage current	-	-	1.0	μA	$V_{DS} = 250V, V_{GS} = -5.0V$
		-	-	200	μA	$V_{DS} = 250V, V_{GS} = -5.0V, T_A = 125^{\circ}C$
I_{DSS}	Saturated drain-to-source current	1.1	-	-	A	$V_{GS} = 0V, V_{DS} = 15V$
$I_{DS(PULSE)}$	Pulsed drain-to-source current	3.1	3.3	-	A	$V_{GS} = 0.9V, V_{DS} = 15V$ with duty cycle of 1%
$R_{DS(ON)}$	Static drain-to-source ON resistance	-	-	3.5	Ω	$V_{GS} = 0V, I_D = 1.0A$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.1	%/°C	$V_{GS} = 0V, I_D = 200mA$
G_{FS}	Forward transconductance	1.0	-	-	mmho	$V_{DS} = 10V, I_D = 150mA$
C_{ISS}	Input capacitance	-	800	1000	pF	$V_{GS} = -2.5V, V_{DS} = 25V, f = 1.0MHz$
C_{OSS}	Common source output capacitance	-	70	210		
C_{RSS}	Reverse transfer capacitance	-	18	70		
$t_{d(ON)}$	Turn-ON delay time	-	-	10	ns	$V_{DD} = 25V, I_D = 150mA, R_{GEN} = 3.0\Omega, V_{GS} = 0V to -10V$
t_r	Rise time	-	-	20		
$t_{d(OFF)}$	Turn-OFF delay time	-	-	10		
t_f	Fall time	-	-	20		
V_{SD}	Diode forward voltage drop	-	-	1.8	V	$V_{GS} = -2.5V, I_{SD} = 150mA$

Typical Performance Curves

Output Characteristics

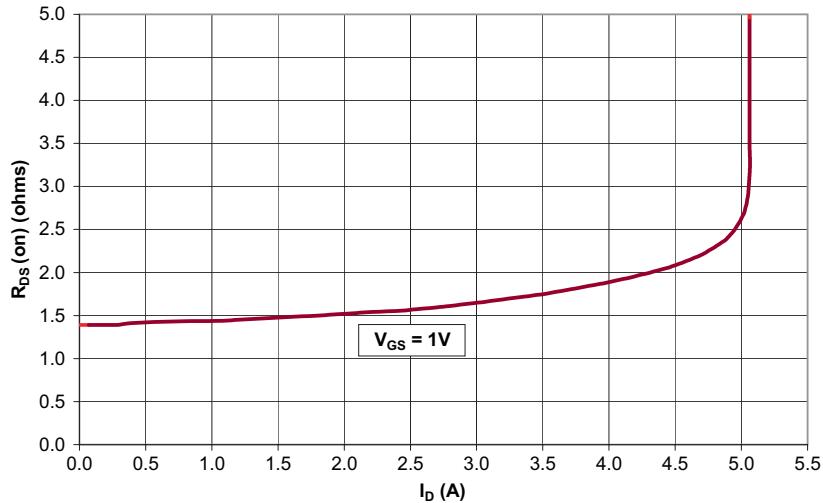


Typical Performance Curves (cont.)

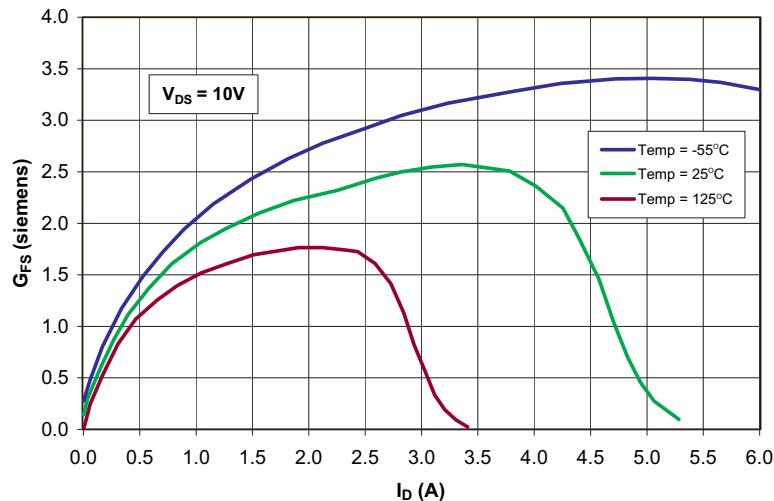
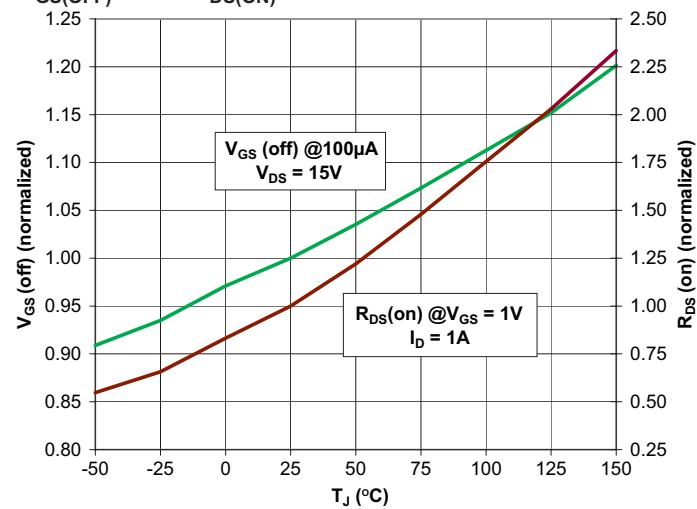


Typical Performance Curves (cont.)

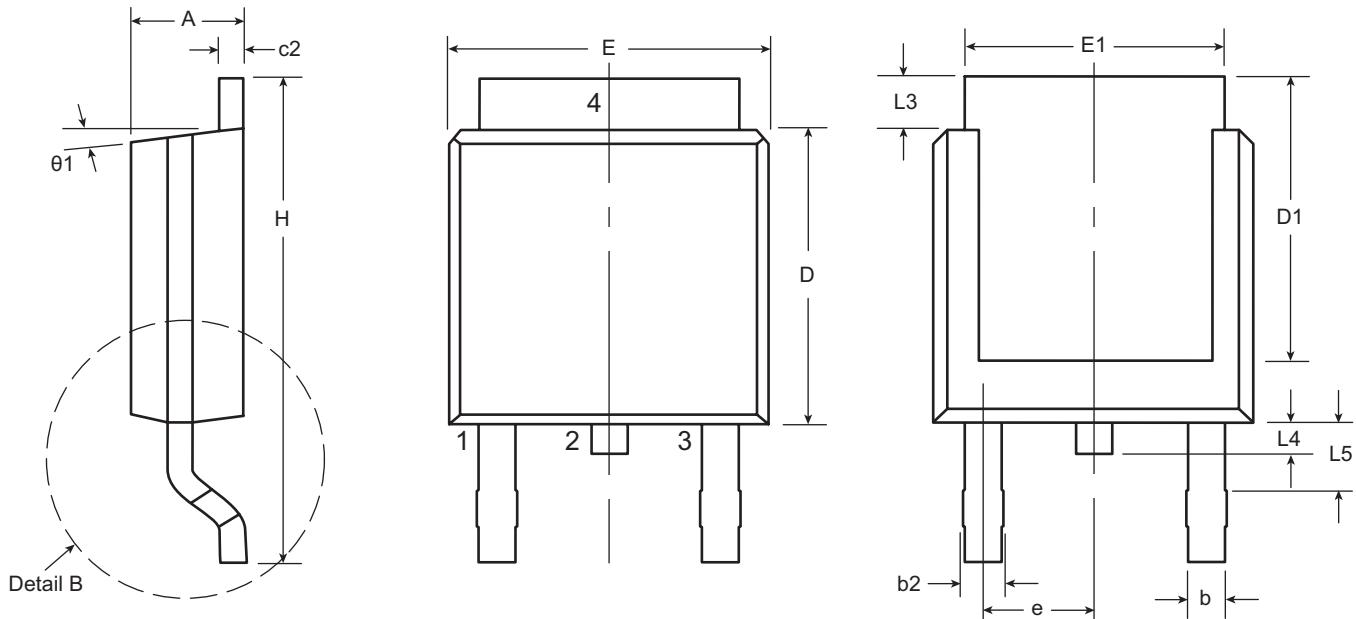
On-Resistance vs Drain Current



Transconductance vs Drain Current

 $V_{GS(OFF)}$ and $R_{DS(ON)}$ Variation With Temperature

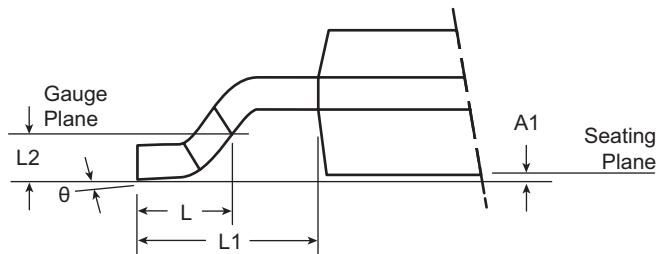
3-Lead TO-252 D-PAK Package Outline (K4)



Side View

Front View

Rear View



Detail B

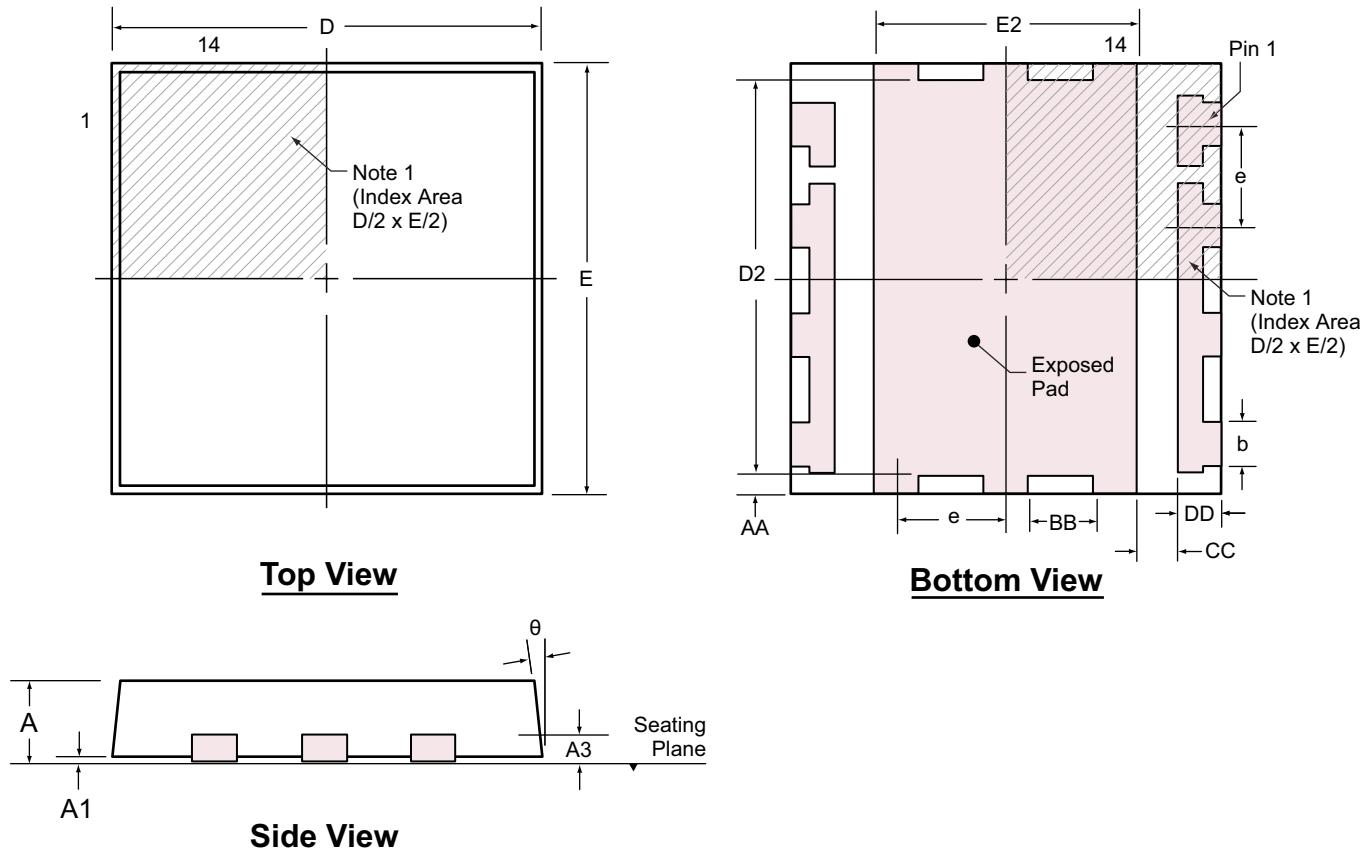
Notes:

1. 4 terminal locations are shown, only 3 are functional. Lead number 2 was removed.

Symbol	A	A1	b	b2	c2	D	D1	E	E1	e	H	L	L1		L3	L4	L5	θ	θ1	
Dimension (inches)	MIN	.086	-	.025	.030	.018	.235	.205	.250	.170	.090 BSC	.370	.055	.108 REF	.020 BSC	.035	-	.045	0°	0°
	NOM	-	-	-	-	-	.240	-	-	-		-	.060			-	-	-	-	-
	MAX	.094	.005	.035	.045	.035	.245	-	.265	-		.410	.070			.050	.040	.060	10°	15°

14-Lead QFN Package Outline (K6)

5x5mm body, 1.0mm height (max), 1.27mm pitch



Notes:

1. Details of Pin 1 identifier are optional, but must be located within the indicated area. The Pin 1 identifier may be either a mold, or a marked feature.

Symbol	A	A1	A3	b	D	D2	E	E2	e	AA	BB	CC	DD	θ	
Dimension (mm)	MIN	0.80	0.00	0.20 REF	0.46	4.85	4.45	4.85	2.52	1.27 BSC	0.152	0.473	0.66	0.456	0°
	NOM	0.90	0.02		0.51	5.00	4.50	5.00	2.57		0.252	0.523	0.71	0.506	-
	MAX	1.00	0.05		0.58	5.15	4.55	5.15	2.62		0.352	0.583	0.77	0.566	14°

Drawings not to scale.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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